



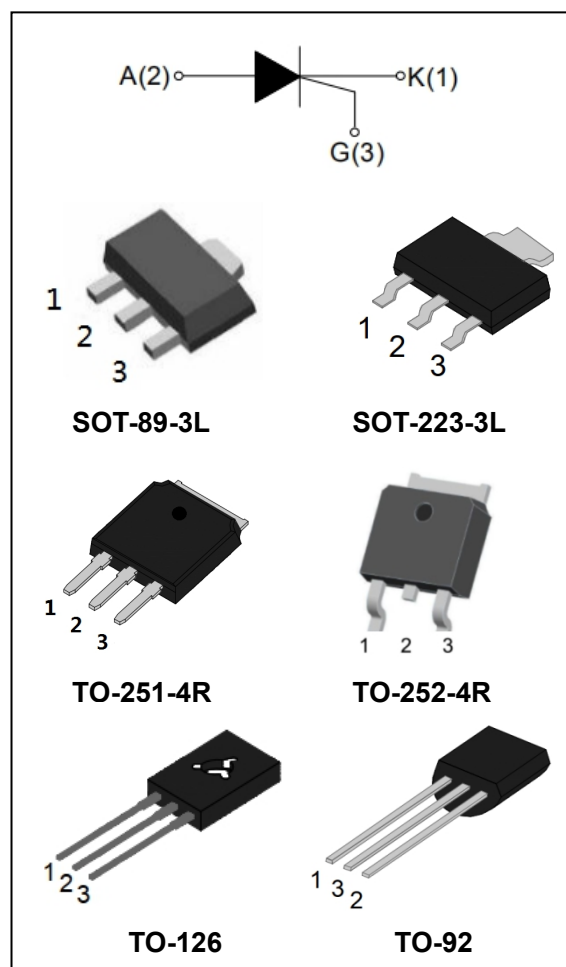
2P4M 2A Sensitive SCRs

DESCRIPTION:

The 2P4M 2A SCR series provide high dv/dt rate with strong resistance to electromagnetic interference. They are especially recommended for use on residual current circuit breaker, straight hair, igniter etc.

MAIN FEATURES:

symbol	value	unit
$I_{T(RMS)}$	2.0	A
I_{GT}	≤ 200	μA
V_{DRM}/V_{RRM}	600	V



ABSOLUTE MAXIMUM RATINGS:

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40~150	$^{\circ}C$
Operating junction temperature range	T_j	-40~110	$^{\circ}C$
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)	V_{RRM}	600	V
RMS on-state current	$I_{T(RMS)}$	2	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)	I_{TSM}	20	A
I^2t value for fusing ($t_p=10ms$)	I^2t	2	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)	di/dt	50	$A/\mu s$



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Peak gate current	I_{GM}	0.2	A
Average gate power dissipation	$P_{G(AV)}$	0.1	W
Peak gate power	P_{GM}	0.5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN	TYPE	MAX	
I_{GT}	$V_D=12\text{V}, R_L=33\Omega$	-	50	200	μA
V_{GT}		-	0.6	0.8	V
V_{GD}	$V_D=V_{DRM} T_j=110^\circ\text{C}$	0.2	-	-	V
I_H	$I_T=50\text{mA}$	-	-	5	mA
I_L	$I_G=1.2I_{GT}$	-	-	6	mA
dV/dt	$V_D=2/3 \times V_{DRM} T_j=110^\circ\text{C} R_{GK}=1\text{K}\Omega$	20	-	-	V/ μs

STATIC CHARACTERISTICS

Symbol	Test Condition			Value	Unit
V_{TM}	$I_{TM}=4\text{A} t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	MAX	1.5	V
I_{DRM} I_{RRM}	$V_D=V_{DRM}=V_{RRM}$ $R_{GK}=1\text{K}\Omega$	$T_j=25^\circ\text{C}$	MAX	5	μA
		$T_j=110^\circ\text{C}$		0.1	mA

THERMAL RESISTANCES

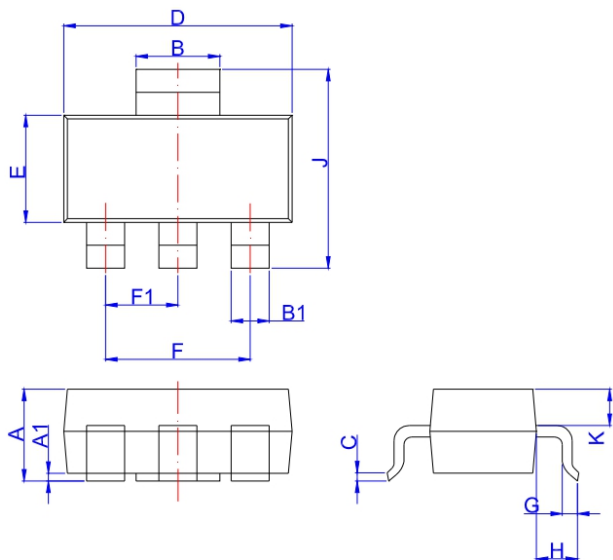
Symbol	Test Condition		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-251-4R/TO-252-4R	6.5	$^\circ\text{C}/\text{W}$
		TO-92	10	
		TO-126	7.0	
		SOT-89-3L	8.3	
		SOT-223-3L	7.3	



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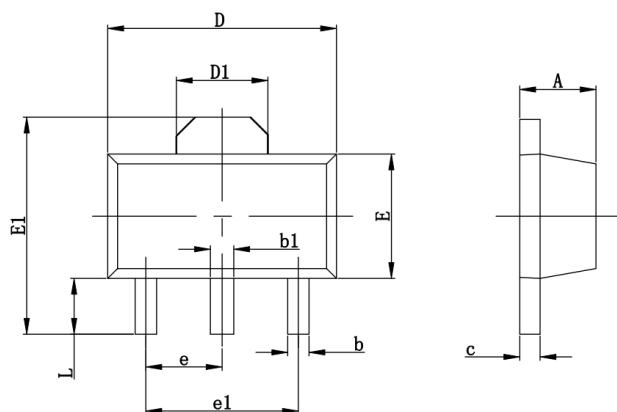
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PACKAGE MECHANICAL DATA



SOT-223

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.5	1.6	1.8	0.059	0.063	0.071
A1	0.01	0.06	0.10	0.001	0.002	0.004
B	2.9	3.0	3.1	0.114	0.118	0.122
B1	0.6	0.7	0.8	0.024	0.028	0.031
C	0.22	0.25	0.32	0.009	0.010	0.013
D	6.3	6.5	6.7	0.248	0.256	0.264
E	3.3	3.5	3.7	0.130	0.138	0.146
F		4.6	6.8	0.252	0.181	
F1		2.3			0.091	
G	0.7	0.9	1.1	0.028	0.035	0.043
H	1.5	1.75	2.0	0.059	0.069	0.079
J	6.7	7.0	7.3	0.264	0.276	0.287
K	0.8	0.9	1.0	0.031	0.035	0.039



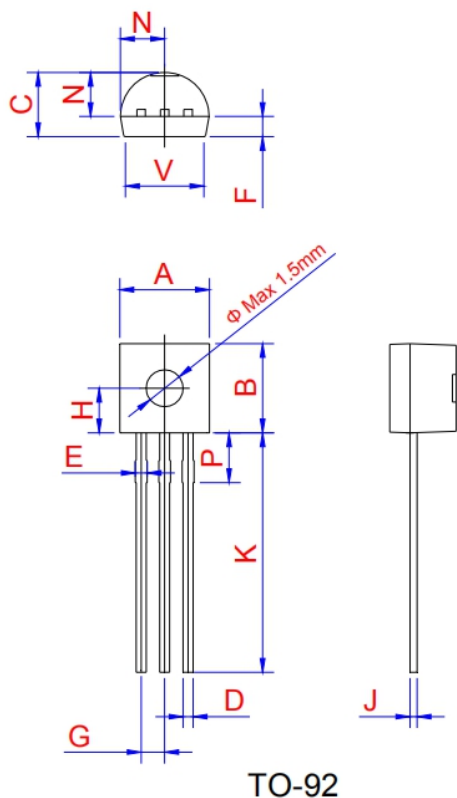
SOT-89-3L

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.4		1.6	0.055		0.063
b	0.35		0.52	0.013		0.197
b1	0.4		0.58	0.016		0.023
c	0.35		0.44	0.014		0.017
D	4.4		4.6	0.173		0.181
D1		1.55			0.061	
E	2.35		2.55	0.091		0.102
E1	3.94		4.25	0.155		0.167
e		1.500			0.060	
e1		3.000			0.118	
L	0.9		1.1	0.035		0.047

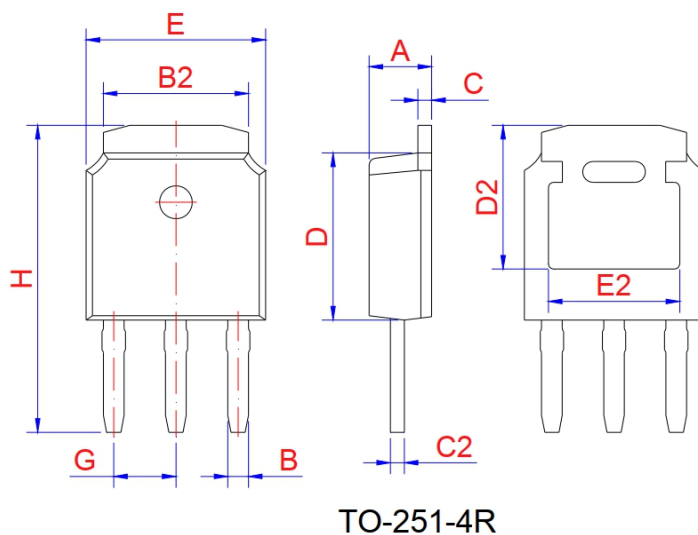


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Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.45	4.6	5.2	0.175	0.181	0.205
B	4.32	4.6	5.33	0.17	0.181	0.21
C	3.18	3.55	4.19	0.125	0.14	0.165
D	0.407		0.533	0.016		0.021
E	0.6		0.8	0.024	0	0.031
F	-	1.1	-	-	0.043	-
G	-	1.27	-	-	0.05	-
H	-	2.3	-	-	0.091	-
J	0.36	0.38	0.5	0.014	0.015	0.02
K	12.7		15	0.5		0.591
N	2.04	2.3	2.66	0.08	0.091	0.105
P	1.86		2.06	0.073		0.081
V	-		4.3	-		0.169

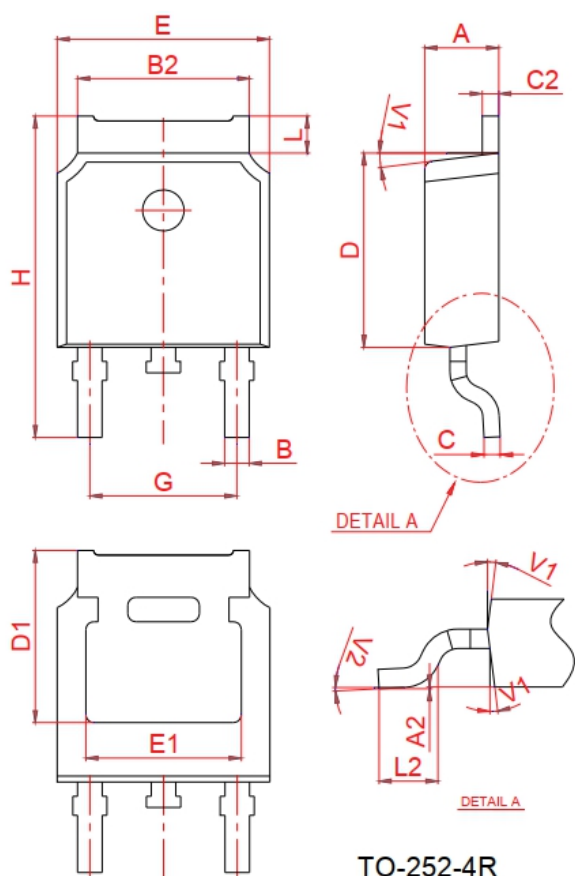


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10	2.30	2.50	0.083	0.091	0.098
B	0.66	0.76	0.86	0.026	0.030	0.034
B2	5.15	5.33	5.48	0.203	0.210	0.216
C	0.44	0.51	0.58	0.017	0.020	0.023
C2	0.44	0.51	0.58	0.017	0.020	0.023
D	5.90	6.10	6.30	0.232	0.240	0.248
D2	5.30REF			0.209REF		
E	6.40	6.60	6.80	0.252	0.260	0.268
E2	4.83REF			0.190REF		
G	2.19	2.29	2.39	0.086	0.090	0.094
H	10.60	11.20	11.80	0.417	0.441	0.465

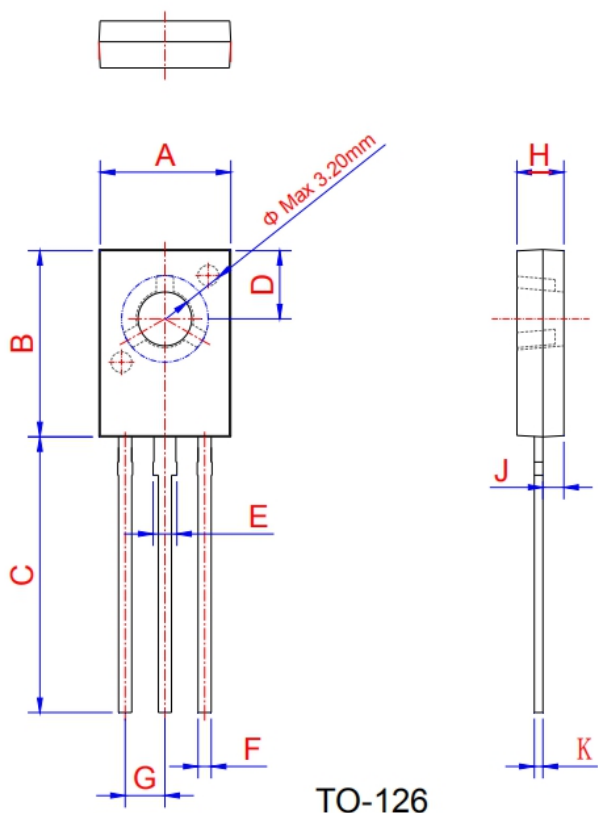


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Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.2		2.4	0.087		0.094
A2	0		0.1	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.1		5.46	0.201		0.215
C	0.46		0.58	0.018		0.023
C2	0.44		0.58	0.017		0.023
D	5.9		6.3	0.232		0.248
D1	5.30REF			0.211REF		
E	6.4		6.8	0.252		0.268
E1	4.63			0.182		
G	4.372		4.772	0.172		0.188
H	9.8		10.4	0.386		0.409
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	7.4		7.8	0.291		0.307
B	10.6		11.2	0.417		0.441
C	15.3		16.3	0.602		0.642
D	3.9		4.1	0.154		0.161
E	1.17		1.47	0.046		0.058
F	0.66		0.86	0.026		0.034
G		2.29			0.09	
H	2.5		2.9	0.098		0.114
K	0.45		0.6	0.018		0.024



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FIG.1: Maximum power dissipation versus RMS on-state current

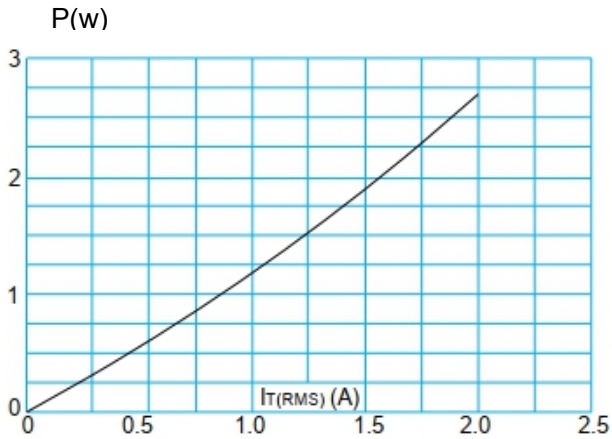


FIG.3: Surge peak on-state current versus number of cycles

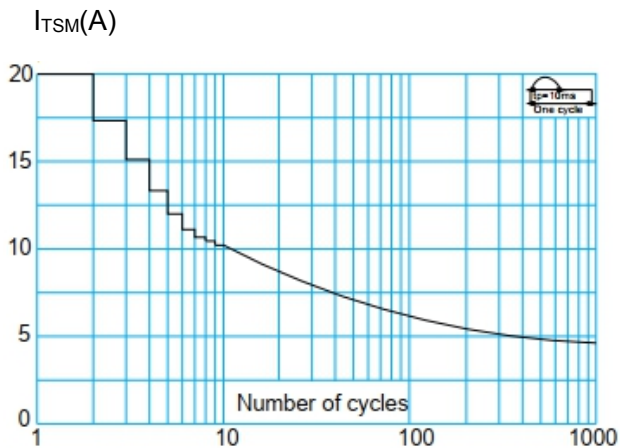


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)

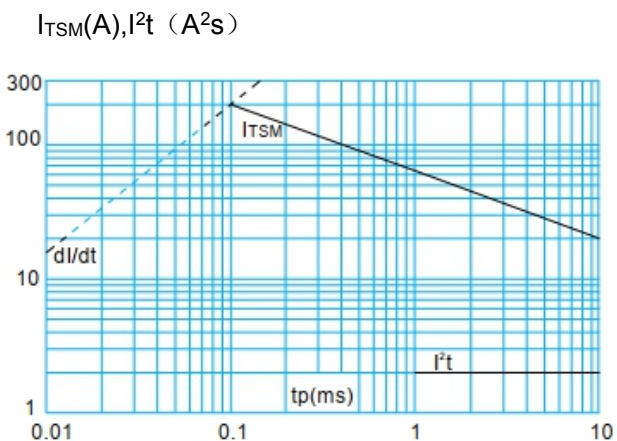


FIG.2: RMS on-state current versus case temperature

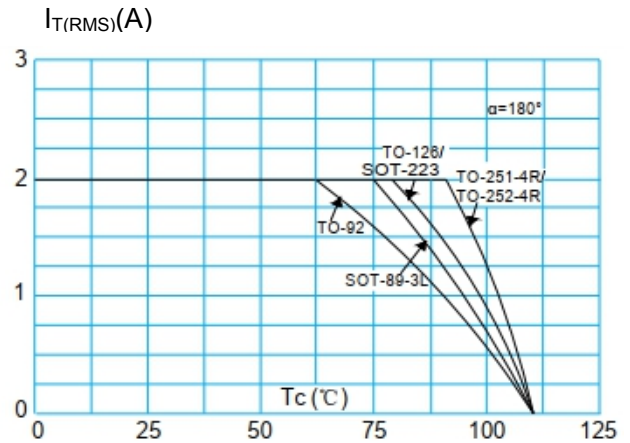


FIG.4: On-state characteristics (maximum values)

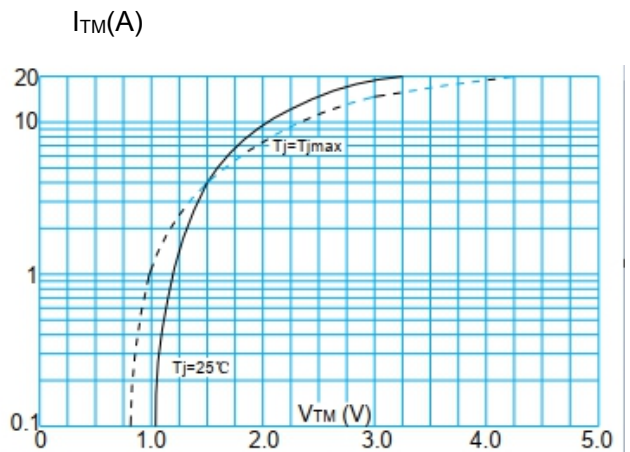
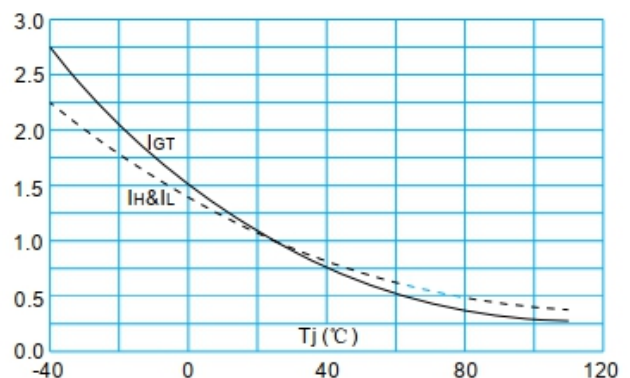


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

$$I_{GT}, I_H, I_L(T_j) / I_{GT}, I_H, I_L(T_j = 25^\circ\text{C})$$





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